Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1. (Cancel)
- 2. (Currently Amended) A-The method of manufacturing a magnetoresistive device according to claim 13, wherein an etchant containing at least one of acid and alkali is used in the wet etching.
- 3. (Currently Amended) A method of manufacturing a magnetoresistive device,

 according to claim 1, wherein the step of comprising the steps of:

 forming a magnetoresistive film on a base, the magnetoresistive film includes

 a step of formingincluding a first ferromagnetic layer, a tunnel barrier layer, and a second

 ferromagnetic layer in order on the baselayer;

 mechanically polishing an end face of the magnetoresistive film; and

 performing wet etching on the mechanically polished end face of the

 magnetoresistive film.
- 4. (Currently Amended) A-The method of manufacturing a magnetoresistive device according to claim 13, further comprising a step of forming a current path for passing a current in a direction perpendicular to an extending surface of the magnetoresistive film.
 - 5. (Cancel)
- 6. (Currently Amended) A-The method of manufacturing a thin film magnetic head according to claim 57, wherein an etchant containing at least one of acid and alkali is used in the wet etching.
- 7. (Currently Amended) A method of manufacturing a thin film magnetic head according to claim 5, wherein the step of comprising the steps of:

forming a reproducing head having a magnetoresistive film on a base, the
magnetoresistive film includes a step of formingincluding a first ferromagnetic layer, a tunnel
barrier layer, and a second ferromagnetic layer in order on a baselayer;
mechanically polishing an end face of the magnetoresistive film; and
performing wet etching on the mechanically polished end face of the
magnetoresistive film.
8. (Currently Amended) A-The method of manufacturing a thin film magnetic head
according to claim 57, wherein the step of forming the reproducing head includes a step of
forming a current path for passing a current in a direction perpendicular to an extending
surface of the magnetoresistive film.
9. (Currently Amended) A-The method of manufacturing a thin film magnetic head
according to claim 57, further comprising a step of forming a recording head on the base
before the step of mechanically polishing the end face.
10. (Cancel)
11. (Currently Amended) A-The method of manufacturing a head assembly
according to claim 1012, wherein an etchant containing at least one of acid and alkali is used
in the wet etching.
12. (Currently Amended) A method of manufacturing a head assembly, according to
claim 10, wherein the step of forming comprising the steps of:
forming a slider having a reproducing head; and
mounting the slider on a slider suspension, wherein the step of forming the
slider comprises the steps of:
forming a reproducing head having a magnetoresistive film on a base, the
magnetoresistive film includes a step of formingincluding a first ferromagnetic layer, a tunnel
barrier layer, and a second ferromagnetic layer in order on the baselayer;

mechanically polishing an end face of the magnetoresistive film; and

performing wet etching on the mechanically polished end face of the

magnetoresistive film.

- 13. (Currently Amended) A-The method of manufacturing a head assembly according to claim 1012, wherein the step of forming the reproducing head includes a step of forming a current path for passing a current in a direction perpendicular to an extending surface of the magnetoresistive film.
- 14. (Currently Amended) A-The method of manufacturing a head assembly according to claim 1012, further comprising a step of forming a recording head on the base before the step of mechanically polishing the end face.